

# Program

Wednesday, February 14th, 2018

from 12:30	Front desk registration
Time	Speaker and Title
13:30	Opening
13:40	<b>J. Derby</b> <b>The synergy of modelling and novel experiments for melt crystal growth research (invited)</b>
14:10	D. Berkov Dislocation-induced stress in polycrystalline materials: mesoscopic simulations
14:30	W. Miller Numerical Investigations on Grain Evolution During Direct Solidification of Silicon
14:50	K.-P. Gradwohl Investigation of twin boundaries in CdZnTe
15:10	Th. Jauß Synchrotron White Beam X-ray Topography Investigation of Particle Incorporation in Silicon
15:30	Coffee break
16:00	<b>A. Bonanni</b> <b>III-nitride modulated epitaxial structures (invited)</b>
16:30	T. Schneider High temperature vapor phase epitaxy for the growth of GaN layers on sapphire substrates
16:50	A. Dittmar PVT growth of bulk $Al_{1-x}Sc_xN$ as lattice matched substrate for AlGaN UV-LEDs
17:10	M. Heuken Epitaxial Technologies for Micro LED
17:40 – 18:30	Award session
19:00	DGKK General Assembly

## Thursday, February 15th, 2018

Time	Speaker and Title
9:00	<b>L. Lymperakis</b> <b>Elastically Frustrated Rehybridization: Implications in Alloy Ordering and Strong Compositional Limitations in Epitaxial InGaN Films (invited)</b>
9:30	B. Epelbaum Morphological stability of growth facets in bulk AlN crystals grown in different crucible materials
9:50	B. Stöger Diffuse scattering of two OD crystals
10:10	X. Yan Crystal growth, structural and thermoelectric properties of the type-I clathrate $Ba_8(Cu,Ga,Ge,\square)_{46}$ ( $\square$ - vacancy)
10:30	Coffee break
11:00	<b>A.A. Haghighirad</b> <b>Novel Materials as the Driver of New Science (invited)</b>
11:30	H. Michor Crystal Growth of $LuNiC_2$ and Studies of its Charge Density Wave Physics
11:50	K. Kliemt Single crystal growth and characterization of Yb compounds
12:10	S. Dzsaber Crossover from Kondo insulator to semimetal by tuning spin-orbit coupling
12:30	Lunch
13:30	<b>A. Lugstein</b> <b>Synthesis and applications of monolithic quasi 1D metal-semiconductor nanowire heterostructures (invited)</b>
14:00	S. Faraji GaN seed layers grown by MOVPE for the purpose of GaN self-separation from sapphire substrate in HVPE
14:20	J. Erlekampf Minority carrier lifetime improvement in n-type 4H-SiC by nitrogen ion implantation
14:50	L. Schmidtner Towards a material parameter based abrasion model for multi-wire sawing of hard and brittle materials
15:10	Coffee break
15:30 - 17:30	Poster session
19:00	Conference Dinner

## Friday, February 16th, 2018

Time	Speaker and Title
9:00	<b>K. Volz</b> <b>What can quantitative electron microscopy do to resolve the secrets of functional materials? (invited)</b>
9:30	S. Kayser Measurement of the local resolution of the Lateral-Photovoltage-Scanning- and Scanning-Photoluminescence-Method
9:50	M. Huszar Electrical characterization of a multi-phase intermetallic TiAl alloy by atomic force microscopy based methods
10:10	L. Stockmeier Edge facet dynamics during the growth of heavily doped n-type silicon by the Czochralski-method
10:30	Coffee break
11:00	<b>Z. Galazka</b> <b>Progress in bulk growth of <math>\beta</math>-Ga<sub>2</sub>O<sub>3</sub> (invited)</b>
11:30	N. Pfändler In-Situ observations of foreign phase particles in fluids and their interaction with the solidification front
12:00	Closing